

# $\mu$ PA2812T1L

RK-UD-11-0117

Rev.1.00

Apr 18, 2012

## P-channel MOS FIELD EFFECT TRANSISTOR

### Description

The  $\mu$  PA2812T1L is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

### Features

- $V_{DSS} -30$  V ( $T_A = 25^\circ\text{C}$ )
- Low on-state resistance  
—  $R_{DS(on)} = 4.8$  m $\Omega$  MAX. ( $V_{GS} = -10$  V,  $I_D = -30$  A)
- 4.5 V Gate-drive available
- Small & thin type surface mount package with heat spreader (8-pin HVSON)
- Pb-free and Halogen free

### Ordering Information

Part No.	LEAD PLATING	PACKING	Package
$\mu$ PA2812T1L-E1-AT	Pure Sn	Tape 3000 p/reel	8-pin HVSON (3333) typ. 0.028 g
$\mu$ PA2812T1L-E2-AT			

### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS} = 0$ V)	$V_{DSS}$	-30	V
Gate to Source Voltage ( $V_{DS} = 0$ V)	$V_{GSS}$	$\pm 20$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\pm 30$	A
Drain Current (pulse) *1	$I_{D(pulse)}$	$\pm 120$	A
Total Power Dissipation *2	$P_{T1}$	1.5	W
Total Power Dissipation (PW = 10 sec) *2	$P_{T2}$	3.8	W
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T3}$	52	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current *3	$I_{AS}$	25	A
Single Avalanche Energy *3	$E_{AS}$	62	mJ

### Thermal Resistance

Channel to Ambient Thermal Resistance *2	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$
Channel to Case (Drain) Thermal Resistance	$R_{th(ch-C)}$	2.4	$^\circ\text{C/W}$

Notes: \*1.  $PW \leq 10$   $\mu\text{s}$ , Duty Cycle  $\leq 1\%$

\*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm

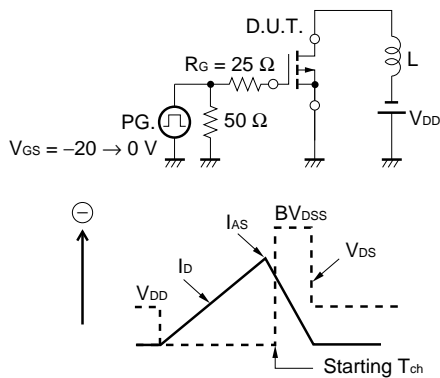
\*3. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = -15$  V,  $R_G = 25$   $\Omega$ ,  $V_{GS} = -20 \rightarrow 0$  V,  $L = 100$   $\mu\text{H}$

**Electrical Characteristics (T<sub>A</sub> = 25°C)**

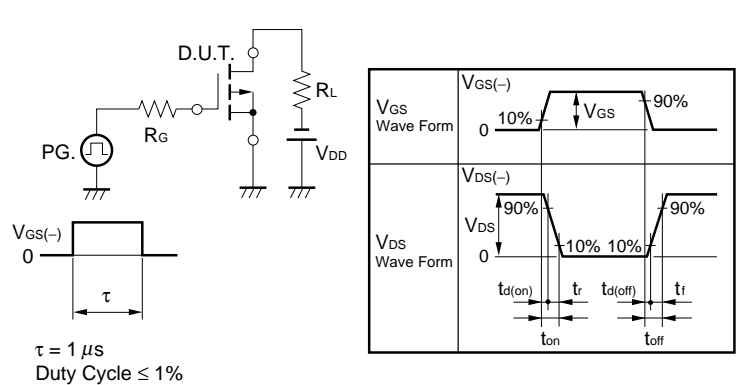
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μA	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V
Gate Leakage Current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Gate Cut-off Voltage	V <sub>GS(off)</sub>	-1.0		-2.5	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance *1	y <sub>fs</sub>	8.0			S	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -15 A
Drain to Source On-state Resistance *1	R <sub>DS(on)1</sub>		3.8	4.8	mΩ	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -30 A
	R <sub>DS(on)2</sub>		6.4	9.9	mΩ	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -15 A
Input Capacitance	C <sub>iSS</sub>		3740		pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz
Output Capacitance	C <sub>oSS</sub>		1780		pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>		1500		pF	
Turn-on Delay Time	t <sub>d(on)</sub>		24		ns	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -15 A, V <sub>GS</sub> = -10 V, R <sub>G</sub> = 10 Ω
Rise Time	t <sub>r</sub>		53		ns	
Turn-off Delay Time	t <sub>d(off)</sub>		180		ns	
Fall Time	t <sub>f</sub>		250		ns	
Total Gate Charge	Q <sub>G</sub>		100		nC	V <sub>DD</sub> = -24 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -30 A
Gate to Source Charge	Q <sub>GS</sub>		11		nC	
Gate to Drain Charge	Q <sub>GD</sub>		48		nC	
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>		0.85		V	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V
Reverse Recovery Time	t <sub>rr</sub>		196		ns	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q <sub>rr</sub>		297		nC	

Note: \*1. Pulsed

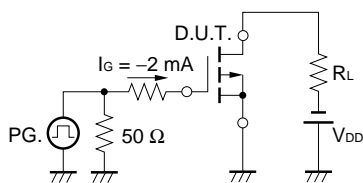
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**

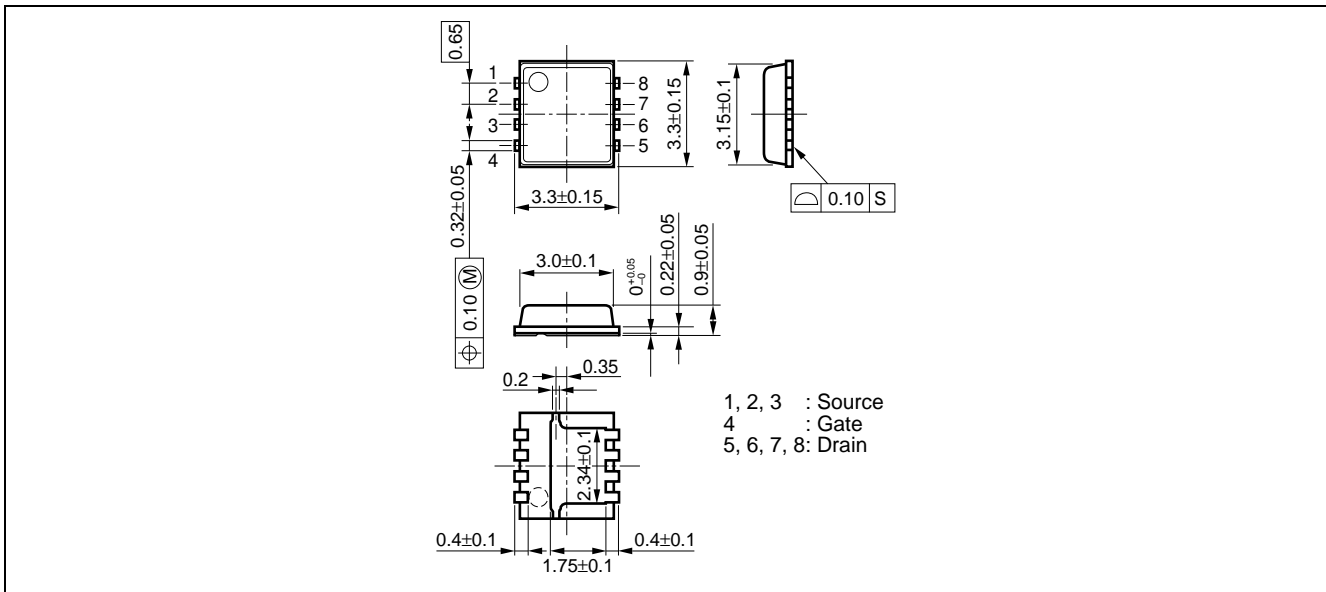


**TEST CIRCUIT 3 GATE CHARGE**

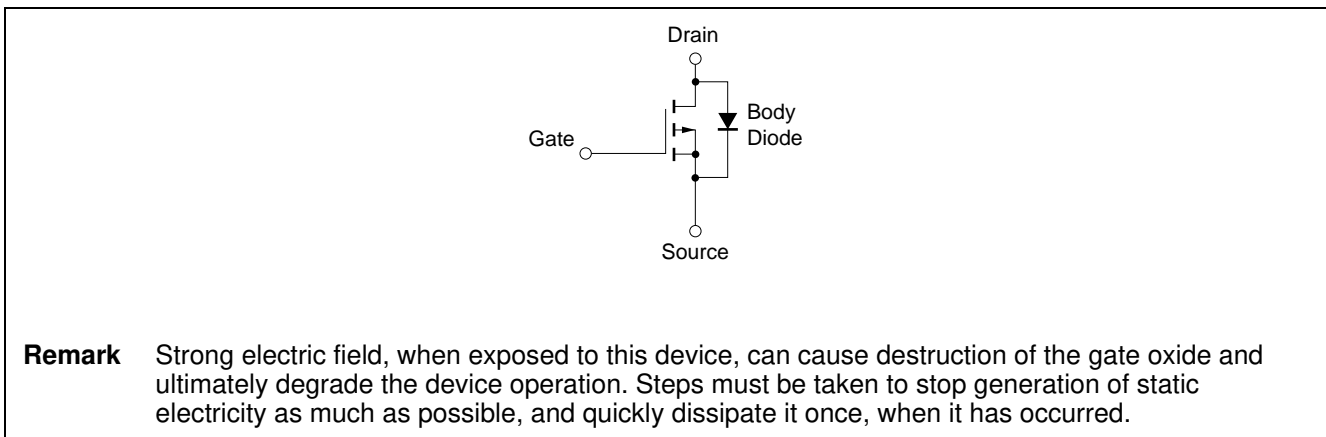


### Package Drawings (Unit: mm)

#### 8-pin HVSON (3333)



### Equivalent Circuit



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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